	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	2	6358800.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:06
2	BRS	12	("5434093" | "5448094" | "5668021" | "5780340" | "6033980" | "6087208" | "6100146" | "6117712" | "6130454" | "6171916" | "6204128" | "6204133").PN.	USPAT	2004/09/12 19:06
3	BRS	1	6358800.URPN.	USPAT	2004/09/12 19:08
4	BRS	9936	transistor with (recess trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:47
5	BRS	1320	transistor with (recess trench) and etching with isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:42
6	BRS	294	transistor near3 (recess trench) and etching near3 ((trench adj isolation) or (STI) or isolation or (field adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:47
7	BRS	1129 3	(gate transistor) near3 (recess trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:47
8	BRS	622	((gate transistor) near3 (recess trench)) and etching near3 ((trench adj isolation) or (STI) or isolation or (field adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:49
9	BRS	42	((gate transistor) near3 (recess trench)) and etching near3 ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:49
10	BRS	758	257/328.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20

	Type	Hits	Search Text	DBs	Time Stamp
11	BRS	611	257/329.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
12	BRS	984	257/330.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
13	BRS	342	257/332.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
14	BRS	188	257/334.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
15	BRS	781	257/336.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
16	BRS	239	257/337.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20